

INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION



(PTO-1449)

ATTY. DOCKET NO.
49657-961

SERIAL NO.
09/769,490

APPLICANT
Kenji ITOGA, et al.

FILING DATE
January 26, 2001

GROUP
2882

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>K</i>	4634643	01/06/1987	SUZUKI	—	—	—

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
<i>K</i>	8-152499	06/11/1996	Japan (w/ English Abstract)	—	—		X
<i>K</i>	0 597 664 A2	05/18/1994	EPO	—	—		X
<i>K</i>	4,634,643	01/06/1987	SUZUKI	—	—	 	
<i>K</i>	0 597 664 A2	05/18/1994	EPO	—	—		X

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

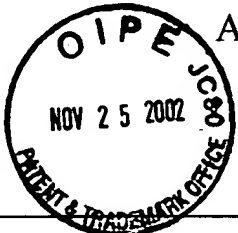

<i>K</i>	"Laser Generated X-Ray Source for Time-Resolved Biological and Material Structure Studies", BARTUNIK et al., Structural Biological Applications of X-Ray Absorption, Scattering, and Diffraction, pp. 331-348, 1996

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION  (PTO-1449)				ATTY. DOCKET NO. 49657-961		SERIAL NO. 09/769,496	
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	"X-Ray nanolithography-the clearest path to 0.1 and sub-0.1um ULSI", M.L. Schattengurg et al, JJAP Series 5, Proc. of 1990 Intern. MicroProcess Conference, pp. 63-70.						
	"Progress of SR lithography-A path to 0.1 micron feature size-", Nobufumi Atoda, International Conference on Advanced Microelectronic Devices and Processing", pp. 103-108, Mar. 3-5, 1994.						
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	"Innovation in ULSI lithography", Tadahiro Takigawa, Naoaki Aizaki, Shinji Okazaki and Kiroaki Morimoto, SCIENCE FORUM, November 10, 1994, pp220-227. (Partial English translation)						
	"Lithography: Exposure system and resist process technology", Shinji Okazaki, Journal of Applied Physics, Vol.69, No.2, (2000) pp.196-200.						
	"Updated system model for x-ray lithography", M. Khan, L. Mohammad, J. Xiao, L. Ocola, and F. Cerrina, J. Vac. Sci. Technol. B 12(6), Nov/Dec 1994, pp.3930-3935.						
	"Sub-Half-Micron Lithography for ULSIs", Katsumi Suzuki, Shinji Matsui and Yukinori Ochiai, Cambridge University Press 2000, pp.66-69						
	"Performance of a wide-flux delivery system for synchrotron x ray lithography", J. P. Silverman, C. N. Archie, J. M. Oberschmidt, and R. P. Rippstein, J. Vac. Sci. Technol. B 11(6), Nov/Dec 1993, pp2976-2980.						
	"Simultaneous optimization of spectrum, spatial coherence, gap, feature bias, and absorber thickness in synchrotron-based x-ray lithography", Scott D. Hector, Henry I. Smith and M. L. Schttenburg, J. Vac. Sci. Technol. B 11(6), Nov/Dec 1993, pp2981-2985.						
	"X ray lithography for <100 nm ground rules in complex patterns", Scott Hector, Victor Pol and Raman Viswanathan et al., J. Vac. Sci. Technol. B 15(6), Nov/Dec 1997, pp2517-2521.						
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	"Fabrication of 0.2um large scale integrated circuits using synchrotron radiation x-ray lithography", K. Deguchi, K. Miyoshi, H. Ban, T. Matsuda, T. Ohno, and Y. Kado, J. Vac. Sci. Technol. B 13(6), Nov/Dec 1995, pp3040-3045.
	"Replication of near 0.1 Φ m hole patterns by using x-ray lithography", Yukiko Kikuchi, Naoko Kihara, Shinji Sugihara, and Satoshi Satoh, et al., J. Vac. Sci. Technol. B 14(6), Nov/Dec 1996, pp4298-4302.
	"Overlay and Critical Dimension Control in Proximity X-ray Lithography", Kiyoshi Fuji, Yuusuke Tanaka, Katsumi Suzuki, Toshiyuki Iwamoto, Shinji Tsuboi and Yasuji Matsui, NEC Research & Development Vol.42, No.1, pp.27-31, January 2001.
	"Control of X-Ray Beam Fluctuation in Synchrotron Radiation Lithography Beamline", Hiroki Shimano, Hirofumi Tanaka, Yoshihiko Ozaki, and Kenji Marumoto, Jpn. J. Appl. Phys. Vol. 34 (1995) pp.5856-5861.
	"Novel illumination system of synchrotron radiation stepper with full field exposure method", Yutaka Watanabe, Shinichi Hara, Nobutoshi Mizusawa, Yasuaki Fukuda and Shunichi Uzawa, J. Vac. Sci. Technol. B 15(6), Nov/Dec (1997), pp.2503-2508.
	"Evaluation of new x-ray stepper, the XRA", Hiroaki Sumitani, Muneyoshi Saita, Soichiro Mitsui, Hajime Aoyama, Kiyoshi Fujii, Hiroshi Watanabe, Takao Taguchi, and Yasuji Matsui, J. Vac. Sci. Technol. B 19(6), Nov/Dec (2001), pp.2448-2454.
	"Parametric modeling at resist-substrate interfaces, L. E. Ocola and F. Cerrina, J. Vac. Sci. Technol. B 12(6), Nov/Dec 1994, pp.3986-3989.

EXAMINER

DATE CONSIDERED



3/12/03

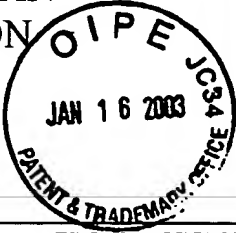










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"Sub-20 nm x-ray nanolithography using conventional mask technologies on monochromatized synchrotron radiation", G. Simon, A. M. Haghiri-Gosnet, J. Bourneix, D. Decanini, Y. Chen, F. Rousseaux, H. Launois, and B. Vidal, J. Vac. Sci. Technol. B15(6), Nov/Dec 1997, pp.2489-2494.							
"The first x ray lithography beamline at Hefei National Synchrotron Radiation Laboratory", Shinan Qian et. al., J. Vac. Sci. Technol. B 8(6), Nov/Dec 1990, pp.1524-1528.							
"Resolution limits in x ray lithography", M. Feldman and J. Sun, J. Vac. Sci. Technol. B 10(6), Nov/Dec 1992, pp.3173-3176.							
"Synchrotron radiation beamline for x ray lithography", Shunji Goto, Takao Taguchi, Toshihiko Osada, Shigeru Okamura, and Tokushige Hisatsugu, J. Vac. Sci. Technol. B 11(2), Mar/Apr 1993, pp.286-295.							
"Extendibility of synchrotron radiation lithography to the sub-100 nm region", Kimiyoshi Deguchi, Kazunori Miyoshi, Masatoshi Oda, Tadahito Matsuda, Akiru Ozawa, and Hideo Yoshihara, J. Vac. Sci. Technol. B 14(6), Nov/Dec 1996, pp.4294-4297.							
"ABSENCE OF RESOLUTION DEGRADATION IN X-RAY LITHOGRAPHY FOR λ FROM 4.5 nm TO 0.83nm", K. Early, M. L. Schattenburg, and Henry I. Smith, Microelectronic Engineering 11 (1990), pp.317-321.							
"International Technology Roadmap for Semiconductors", (1999). pp. p154 Fig.23, http://public.itrs.net/Files/1999_SIA_Roadmap/Litho.pdf .							
"X ray lithography source using a stationary solid Pd target ", J. R. Maldonado, M. E. Poulsen, T. E. Saunders, F. Vratny, and A. Zacharias, J. Vac. Sci. Technol. 16, No. 6, Nov/Dec. 1979, pp.1942-1945.							
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"SOR Lithography", T. Hosokawa, T. Hayasaka, H. Yoshihara, S. Ishihara, and T. Kitayama, Jpn. J. Appl. Phys. Proc. Of 1989 Intern. Symp. On MicroProcess Conference, Plaintiff:72-75.							
"Proposal for a 50 nm proximity x-ray lithography system and extension to 36 nm by resist material selection", Toyoki Kitayama Kenji Itoga, Yutaka Watanabe and Shunichi Uzawa, J. Vac. Sci. Technol. B 18(6), Nov/Dec 2000 pp.2950-2954.							
"Technology and performance of the Canon XRA-1000 production x-ray stepper", Nobutoshi Mizusawa, Kouji Uda, Yutaka Tanaka, Hirohisa Ohta and Yutaka Watanabe, J. Vac. Sci. Technol. B 18(6), Nov/Dec 2000, pp.2955-2960.							
"Extension of x-ray lithography to 50 nm with a harder spectrum", M. Khan, G. Han, S. B. Bollepalli, F. Cerrina and J. Maldonado, J. Vac. Sci. Technol. B 17(6), Nov/Dec 1999, pp.3426-3432.							
"Can proximity x-ray lithography print 35 nm features ? Yes", Mumit Khan, Geng Han, Gene Tsvi, Toyoki Kitayama, Juan Muldonado, and Franco Cerrina, J. Vac. Sci. Technol. B 19(6), Nov/Dec 2001, pp.2423-2427.							
"Effect of secondary electron from the substrate in x-ray lithography using harder radiation spectra", K. Itoga, K. Marumoto, T. Kitayama, H. Sumitani, M. Amemiya, and Y. Watanabe, J. Vac. Sci. Technol. B 19(6), Nov/Dec 2001, pp.2439-2443.							
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(PTO-1449) <div style="position: absolute; top: 50px; left: 50px; border: 1px solid black; border-radius: 50%; padding: 10px; text-align: center;"> NO I P E JAN 16 2003 USPTO PATENT & TRADEMARK OFFICE </div>				APPLICANT Kenji ITOGA, et al.			
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	"Innovation in ULSI lithography", Tadahiro Takigawa, Naoaki Aizaki, Shinji Okazaki and Hiroaki Morimoto, SCIENCE FORUM, November 10, 1994, pp220-227. (Partial English translation)						
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